

# David E Aspnes

## List of Publications by Year in descending order

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218  
papers

17,463  
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19636

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130  
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219  
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219  
docs citations

219  
times ranked

8810  
citing authors

#	ARTICLE	IF	CITATIONS
1	Classical Model of Surface Enhanced Infrared Absorption (SEIRA) Spectroscopy. Journal of Physical Chemistry A, 2022, , .	1.1	2
2	Maximum-entropy revisited: Optimal filtering of spectra. Journal of Applied Physics, 2021, 129, .	1.1	8
3	Classical Correlation Model of Resonance Raman Spectroscopy. Journal of Physical Chemistry A, 2020, 124, 9177-9186.	1.1	1
4	Extended Gaussian Filtering for Noise Reduction in Spectral Analysis. Journal of the Korean Physical Society, 2020, 77, 819-823.	0.3	9
5	Critical Test of the Interaction of Surface Plasmon Resonances with Molecular Vibrational Transitions. Journal of Physical Chemistry A, 2020, 124, 1744-1753.	1.1	2
6	Quantitative assessment of linear noise-reduction filters for spectroscopy. Optics Express, 2020, 28, 38917.	1.7	7
7	Combined interpolation, scale change, and noise reduction in spectral analysis. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 052903.	0.6	18
8	Linear and nonlinear filtering of spectra. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 051205.	0.6	12
9	Dielectric Functions and Critical Points of GaAsSb Alloys. Journal of the Korean Physical Society, 2019, 74, 595-599.	0.3	3
10	Liquid gallium and the eutectic gallium indium (EGaIn) alloy: Dielectric functions from 1.24 to 3.1 eV by electrochemical reduction of surface oxides. Applied Physics Letters, 2016, 109, .	1.5	42
11	Exciton-dominated Dielectric Function of Atomically Thin MoS <sub>2</sub> Films. Scientific Reports, 2015, 5, 16996.	1.6	155
12	Bond models in linear and nonlinear optics. Proceedings of SPIE, 2015, , .	0.8	2
13	Parameterization of the dielectric functions of InGaSb alloys. Current Applied Physics, 2014, 14, 768-771.	1.1	2
14	Interband transitions and dielectric functions of InGaSb alloys. Applied Physics Letters, 2013, 102, .	1.5	6
15	Spectroscopic ellipsometryâ€”A perspective. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	0.9	29
16	Shallow acceptor complexes in p-type ZnO. Applied Physics Letters, 2013, 102, .	1.5	116
17	Plasmonics and Effective-Medium Theory. , 2013, , 203-224.		2
18	Optical and structural characterization of epitaxial graphene on vicinal 6H-SiC(0001)â€”Si by spectroscopic ellipsometry, Auger spectroscopy, and STM. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	21

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19	Control of the oxidation kinetics of H-terminated (111)Si by using the carrier concentration and the strain: a second-harmonic-generation investigation. Journal of the Korean Physical Society, 2012, 60, 1685-1689.	0.3	1
20	Bond-specific reaction kinetics during the oxidation of (111) Si: Effect of n-type doping. Applied Physics Letters, 2011, 98, .	1.5	8
21	Effect of strain on bond-specific reaction kinetics during the oxidation of H-terminated (111) Si. Applied Physics Letters, 2011, 98, 121912.	1.5	8
22	Measurement and Control of In-Plane Surface Chemistry During Oxidation of H-Terminated (111)Si. AIP Conference Proceedings, 2011, . .	0.3	0
23	Analysis of surface roughness of critical-dimension structures using spectroscopic ellipsometry. AIP Conference Proceedings, 2011.	0.3	0
24	Above-band-gap dielectric functions of ZnGeAs <sub>2</sub> : Ellipsometric measurements and quasiparticle self-consistent	1.1	10
25	Back-reflection Second-harmonic Generation of (111)Si: Theory and Experiment. Journal of the Korean Physical Society, 2011, 58, 1237-1243.	0.3	3
26	Roughness Analysis of the Critical Dimension by Using Spectroscopic Ellipsometry. Journal of the Korean Physical Society, 2011, 58, 1426-1428.	0.3	1
27	Bond models in linear and nonlinear optics. Physica Status Solidi (B): Basic Research, 2010, 247, 1873-1880.	0.7	8
28	Thickness inhomogeneities and growth mechanisms of GaP heteroepitaxy by organometallic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 583-589.	0.9	1
29	Dielectric functions and interband transitions of In <sub>1-x</sub> Al <sub>x</sub> Sb alloys. Applied Physics Letters, 2010, 97, .	1.5	6
30	Chemical-etch-assisted growth of epitaxial zinc oxide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 689-692.	0.9	0
31	Ellipsometric study of single-crystal <sup>13</sup> InSe from 1.5 to 9.2 eV. Applied Physics Letters, 2010, 96, 181902.	1.5	13
32	Nondestructive analysis of coated periodic nanostructures from optical data. Optics Letters, 2010, 35, 733.	1.7	1
33	Measurement and control of in-plane surface chemistry during the oxidation of H-terminated (111) Si. Proceedings of the National Academy of Sciences of the United States of America, 2010, 107, 17503-17508.	3.3	18
34	Interband transitions of InAs <sub>x</sub> Sb <sub>1-x</sub> alloy films. Applied Physics Letters, 2009, 95, 111902.	1.5	24
35	Analytical solution of thickness variations in selective area growth by organometallic chemical vapor deposition. Applied Physics Letters, 2009, 94, 253112.	1.5	4
36	Plasmonic phenomena in indium tin oxide and ITO-Au hybrid films. Optics Letters, 2009, 34, 2867.	1.7	103

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37	Follow the light: Ellipsometry and polarimetry. <i>Physics Today</i> , 2009, 62, 70-71.	0.3	3
38	Investigation of heteroepitaxy on nanoscopically roughened (001)Si by real-time spectroscopic polarimetry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 1312-1315.	0.8	1
39	The anisotropic bond model of nonlinear optics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 728-731.	0.8	4
40	Dielectric properties of InAsP alloy thin films and evaluation of direct- and reciprocal-space methods of determining critical-point parameters. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 884-887.	0.8	3
41	The nearly aligned rotating-monoplate compensator. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 739-742.	0.8	2
42	Optical properties of In <sub>x</sub> Al <sub>1-x</sub> As alloy films. <i>Applied Physics Letters</i> , 2008, 92, 151907.	1.5	14
43	Application of the anisotropic bond model to second-harmonic generation from amorphous media. <i>Physical Review B</i> , 2008, 77, .	1.1	23
44	Overlayer effects in the critical-point analysis of ellipsometric spectra: Application to In <sub>x</sub> Ga <sub>1-x</sub> As alloys. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	4
45	Thickness inhomogenities in the organometallic chemical vapor deposition of GaP. <i>Applied Physics Letters</i> , 2008, 93, 203104.	1.5	4
46	Dependence of plasmon polaritons on the thickness of indium tin oxide thin films. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	149
47	Model dielectric functions for Al <sub>x</sub> Ga <sub>1-x</sub> As alloys of arbitrary compositions. <i>Journal of Applied Physics</i> , 2008, 104, 013515.	1.1	13
48	Initial stages of GaP heteroepitaxy on nanoscopically roughened (001)Si. <i>Journal of Vacuum Science &amp; Technology B</i> , 2007, 25, 1448.	1.3	7
49	Analytic determination of $n$ , $\hat{\epsilon}$ , and $d$ of an absorbing film from polarimetric data in the thin-film limit. <i>Journal of Applied Physics</i> , 2007, 101, 033109.	1.1	15
50	Effect of overlayers on critical-point parameters in the analysis of ellipsometric spectra. <i>Applied Physics Letters</i> , 2007, 91, 121903.	1.5	15
51	Investigation of effective-medium approximation, alloy, average-composition, and graded-composition models for interface analysis by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 2007, 102, 063512.	1.1	7
52	Dielectric functions and electronic structure of InAs <sub>x</sub> P <sub>1-x</sub> films on InP. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	16
53	Electrodynamic Properties of Nanoscopically Inhomogeneous Materials. <i>AIP Conference Proceedings</i> , 2007, , .	0.3	0
54	Toward $n^{\hat{e}}d$ spectroscopy: Analytic solution of the three-phase model of polarimetry in the thin-film limit. <i>Applied Physics Letters</i> , 2006, 88, 201107.	1.5	5

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55	Systematic approach for analyzing reflectance-difference spectra: Application to silicon-dielectric interfaces. Applied Physics Letters, 2006, 88, 202112.	1.5	7
56	Differences Between Charge Trapping States in Irradiated Nano-Crystalline HfO <sub>2</sub> and Non-Crystalline Hf Silicates. IEEE Transactions on Nuclear Science, 2006, 53, 3644-3648.	1.2	26
57	Real-time diagnostics for metalorganic vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2005, 242, 2551-2560.	0.7	5
58	Optical properties of (GaSb) <sub>3n</sub> (AlSb) <sub>n</sub> (1 ≤ n ≤ 5) superlattices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1149.	1.6	0
59	Dipole-radiation model for terahertz radiation from semiconductors. Applied Physics Letters, 2005, 86, 212109.	1.5	1
60	Relative bulk and interface contributions to optical second-harmonic generation in silicon. Physical Review B, 2005, 72, .	1.1	17
61	Dielectric functions of Al <sub>x</sub> Ga <sub>1-x</sub> Sb (0.00 ≤ x ≤ 0.39) alloys from 1.5 to 6.0 eV. Journal of Applied Physics, 2005, 98, 104108.	1.1	4
62	Real-time characterization of GaSb homo- and heteroepitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2233.	1.6	2
63	Spectroscopic ellipsometric analysis of interfaces: Comparison of alloy and effective-medium-approximation approaches to a CdMgTe multilayer system. Applied Physics Letters, 2004, 85, 946-948.	1.5	4
64	Calculation of bulk third-harmonic generation from crystalline Si with the simplified bond hyperpolarizability model. Physical Review B, 2004, 70, .	1.1	14
65	Optical properties of Cd <sub>1-x</sub> Mg <sub>x</sub> Te (x=0.00, 0.23, 0.31, and 0.43) alloy films. Applied Physics Letters, 2004, 84, 693-695.	1.5	12
66	Optimizing precision of rotating-analyzer and rotating-compensator ellipsometers. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 2004, 21, 403.	0.8	32
67	Simplified bond-hyperpolarizability model of second- and fourth-harmonic generation: application to Si/SiO <sub>2</sub> interfaces. Physica Status Solidi (B): Basic Research, 2003, 240, 509-517.	0.7	2
68	Dielectric functions of In <sub>x</sub> Ga <sub>1-x</sub> As alloys. Physical Review B, 2003, 68, .	1.1	43
69	Application of the simplified bond-hyperpolarizability model to fourth-harmonic generation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1798.	1.6	9
70	Pseudodielectric function of ZnGeP <sub>2</sub> from 1.5 to 6 eV. Applied Physics Letters, 2002, 81, 628-630.	1.5	4
71	Simplified bond-hyperpolarizability model of second harmonic generation. Physical Review B, 2002, 65, .	1.1	69
72	Simplified bond-hyperpolarizability model of second harmonic generation: Application to Si-dielectric interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1699.	1.6	20

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73	Pseudodielectric functions of InGaAs alloy films grown on InP. Applied Physics Letters, 2002, 81, 2367-2369.	1.5	9
74	Nondestructive Measurement of a Glass Transition Temperature at Spin-Cast Semicrystalline Polymer Surfaces. Macromolecules, 2001, 34, 2395-2397.	2.2	19
75	Determination and Critical Assessment of the Optical Properties of Common Substrate Materials Used in III-V Nitride Heterostructures with Vacuum Ultraviolet Spectroscopic Ellipsometry. Materials Research Society Symposia Proceedings, 2001, 693, 745.	0.1	1
76	Elimination of endpoint-discontinuity artifacts in the analysis of spectra in reciprocal space. Journal of Applied Physics, 2001, 89, 8183-8192.	1.1	26
77	Ordinary and extraordinary dielectric functions of 4H and 6H-SiC from 3.5 to 9.0 eV. Applied Physics Letters, 2001, 78, 2715-2717.	1.5	25
78	Investigation of noise in a spectrometer system using a short-arc source. Review of Scientific Instruments, 2001, 72, 3477-3479.	0.6	4
79	Ordinary and Extra-Ordinary Dielectric Function of 4h- and 6H-SiC in the 0.7 to 9.0 eV Photon Energy Range. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	1
80	Effect of Ar <sup>+</sup> ion beam in the process of plasma surface modification of PET films. Journal of Applied Polymer Science, 2000, 77, 1679-1683.	1.3	17
81	Real-time optical techniques and QMS to characterize growth in a modified commercial OMVPE reactor. Journal of Electronic Materials, 2000, 29, 106-111.	1.0	4
82	Surface-induced optical anisotropy of Si and Ge. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2229.	1.6	14
83	Isotopic effects on the dielectric response of Si around the E <sub>1</sub> gap. Physical Review B, 2000, 61, 12946-12951.	1.1	32
84	Visible-near ultraviolet ellipsometric study of Zn <sub>1-x</sub> Mg <sub>x</sub> Se and Zn <sub>1-x</sub> Be <sub>x</sub> Se alloys. Journal of Applied Physics, 2000, 88, 878-882.	1.1	21
85	Real-time optical characterization of heteroepitaxy by organometallic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1184-1189.	0.9	16
86	Optical properties of Al <sub>x</sub> Ga <sub>1-x</sub> P <sub>0.52</sub> alloys. Journal of Applied Physics, 2000, 87, 1287-1290.	1.1	26
87	Dielectric function of epitaxial ZnSe films. Applied Physics Letters, 2000, 77, 3364-3366.	1.5	11
88	Combined beam profile reflectometry, beam profile ellipsometry and ultraviolet-visible spectrophotometry for the characterization of ultrathin oxide-nitride-oxide films on silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 380-384.	0.9	15
89	Comment on "Ab Initio Calculation of Excitonic Effects in the Optical Spectra of Semiconductors". Physical Review Letters, 1999, 83, 3970-3970.	2.9	24
90	Analysis of high-index Si(001) surfaces by reflectance difference spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1652-1656.	0.9	4

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91	High-Resolution Spectroscopy with Reciprocal-Space Analysis. Physica Status Solidi (B): Basic Research, 1999, 215, 715-723.	0.7	7
92	Photon-induced localization and final-state correlation effects in optically absorbing materials. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2367.	1.6	14
93	Reflectance difference spectroscopy spectra of clean (3Å-2), (2Å-1), and c(2Å-2)â€%3C-SiC(001) surfaces: New evidence for surface state contributions to optical anisotropy spectra. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2355.	1.6	15
94	Analytic representations of the dielectric functions of crystalline and amorphous Si and crystalline Ge for very large scale integrated device and structural modeling. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 1654-1657.	0.9	22
95	Trends in residual stress for GaN/AlN/6Hâ€“SiC heterostructures. Applied Physics Letters, 1998, 73, 2808-2810.	1.5	41
96	Relaxation Phenomena in GaN/ AlN/ 6H-SiC Heterostructures. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
97	Evidence of near-surface localization of excited electronic states in crystalline Si. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1196.	1.6	25
98	Surface and interface effects on ellipsometric spectra of crystalline Si. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1205.	1.6	25
99	Ellipsometric studies of Cd1âˆ“xMgxTe (0âˆ“1/2xâˆ“1/20.5) alloys. Applied Physics Letters, 1997, 71, 249-251.	1.5	23
100	Low pH Chemical Etch Route for Smooth H-Terminated Si(100) And Study Of Subsequent Chemical Stability. Materials Research Society Symposia Proceedings, 1997, 477, 191.	0.1	0
101	Spectroscopic ellipsometric characterization of undoped ZnTe films grown on GaAs. Applied Physics Letters, 1997, 70, 610-612.	1.5	34
102	Variation of GaN valence bands with biaxial stress and quantification of residual stress. Applied Physics Letters, 1997, 70, 2001-2003.	1.5	51
103	Realâ€time assessment of overlayer removal on GaN, AlN, and AlGaIn surfaces using spectroscopic ellipsometry. Applied Physics Letters, 1996, 69, 2065-2067.	1.5	58
104	Real-time optical diagnostics for epitaxial growth. AIP Conference Proceedings, 1996, , .	0.3	1
105	<title>Real-time optical diagnostics for epitaxial growth</title>. , 1996, , .		2
106	Growth, Doping and Characterization of Al<sub>x</sub>Ga<sub>1âˆ“x</sub>N Thin Film Alloys on 6H-SiC(0001) Substrates. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	101
107	Multilevel Approaches Toward Monitoring and Control of Semiconductor Epitaxy. Materials Research Society Symposia Proceedings, 1996, 448, 451.	0.1	1
108	Variation of GaN Valence Bands with Biaxial Stress: Quantification of Residual Stress and Impact on Fundamental Band Parameters. Materials Research Society Symposia Proceedings, 1996, 449, 781.	0.1	2

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109	In-Plane Optical Anisotropies of Al <sub>x</sub> Ga <sub>1-x</sub> N films in their Regions of Transparency. Materials Research Society Symposia Proceedings, 1996, 449, 835.	0.1	2
110	Optical approaches to determine near-surface compositions during epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 960-966.	0.9	37
111	Reciprocal-space analysis of photoluminescence and photoluminescence excitation spectra. Applied Physics Letters, 1996, 68, 3230-3232.	1.5	4
112	Optical investigations of surface processes in GaP heteroepitaxy on silicon under pulsed chemical beam epitaxy conditions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 3040.	1.6	9
113	New approach to preparing smooth Si(100) surfaces: Characterization by spectroellipsometry and validation of Si/SiO <sub>2</sub> interfaces properties in metal-oxide-semiconductor devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2812.	1.6	7
114	Analysis of Strain in GaN on Al <sub>2</sub> O <sub>3</sub> and 6H-SiC: Near-Bandedge Phenomena. Materials Research Society Symposia Proceedings, 1995, 395, 405.	0.1	7
115	Real-time Optical Monitoring of GaIn <sub>x</sub> P/GaP Heterostructures on Silicon. Materials Research Society Symposia Proceedings, 1995, 406, 127.	0.1	0
116	In-Situ and Ex-Situ Studies of Silicon Interfaces and Nanostructures by Ellipsometry and Rds. Materials Research Society Symposia Proceedings, 1995, 406, 371.	0.1	1
117	Investigation of the relationship between reflectance difference spectroscopy and surface structure using grazing incidence X-ray scattering. Physica Status Solidi A, 1995, 152, 9-21.	1.7	33
118	Real-Time Observation of Atomic Ordering in (001)In <sub>0.53</sub> Ga <sub>0.47</sub> As Epitaxial Layers. Physical Review Letters, 1995, 74, 3640-3643.	2.9	42
119	Performance capabilities of reflectometers and ellipsometers for compositional analysis during Al <sub>x</sub> Ga <sub>1-x</sub> As epitaxy. Applied Physics Letters, 1995, 66, 1617-1619.	1.5	8
120	Surface-Induced Optical Anisotropies of Single-Domain(2 $\times$ 1)Reconstructed (001) Si and Ge Surfaces. Physical Review Letters, 1995, 74, 3431-3434.	2.9	114
121	As capture and the growth of ultrathin InAs layers on InP. Applied Physics Letters, 1994, 64, 3279-3281.	1.5	17
122	As capture and the growth of ultrathin InAs layers on InP. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1994, 12, 1180-1185.	0.9	10
123	Study of strain and disorder of In <sub>x</sub> Ga <sub>1-x</sub> P/(GaAs, graded GaP) (0.25 $\leq$ x $\leq$ 0.8) using spectroscopic ellipsometry and Raman spectroscopy. Journal of Applied Physics, 1994, 75, 5040-5051.	1.1	52
124	Optical-standard surfaces of single-crystal silicon for calibrating ellipsometers and reflectometers. Applied Optics, 1994, 33, 7435.	2.1	77
125	Optical anisotropy of singular and vicinal Si $\text{--}$ SiO <sub>2</sub> interfaces and H-terminated Si surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1994, 12, 1152-1157.	0.9	76
126	Minimal-data approaches for determining outer-layer dielectric responses of films from kinetic reflectometric and ellipsometric measurements. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 1993, 10, 974.	0.8	126



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127	Optical study of $(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{In}_{0.5}\text{P}/\text{GaAs}$ semiconductor alloys by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 1993, 73, 400-406.	1.1	26
128	Minimal data approaches for determining outer layer dielectric responses of films from kinetic reflectometric and ellipsometric measurements. <i>Applied Physics Letters</i> , 1993, 62, 343-345.	1.5	30
129	Real-Time Surface and Near-Surface Optical Diagnostics for Epitaxial Growth. <i>Materials Research Society Symposia Proceedings</i> , 1993, 324, 3.	0.1	4
130	Optical dielectric response of PdO. <i>Physical Review B</i> , 1992, 46, 15085-15091.	1.1	17
131	Growth of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ parabolic quantum wells by real-time feedback control of composition. <i>Applied Physics Letters</i> , 1992, 60, 1244-1246.	1.5	116
132	Formation of The Interface between InP and Arsenic Based Alloys by Chemical Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1992, 263, 267.	0.1	5
133	Surface science at atmospheric pressure: Reconstructions on (001) GaAs in organometallic chemical vapor deposition. <i>Physical Review Letters</i> , 1992, 68, 627-630.	2.9	223
134	Reflectance-difference spectroscopy of (001) GaAs surfaces in ultrahigh vacuum. <i>Physical Review B</i> , 1992, 46, 15894-15904.	1.1	326
135	Real-time optical diagnostics for epitaxial growth. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1991, 9, 870-875.	0.9	14
136	In situ determination of free carrier concentrations by reflectance difference spectroscopy. <i>Applied Physics Letters</i> , 1991, 59, 3443-3445.	1.5	86
137	Optical control of growth of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ by organometallic molecular beam epitaxy. <i>Applied Physics Letters</i> , 1990, 57, 2707-2709.	1.5	74
138	Application of ellipsometry to crystal growth by organometallic molecular beam epitaxy. <i>Applied Physics Letters</i> , 1990, 56, 2569-2571.	1.5	114
139	Direct optical measurement of surface dielectric responses: Interrupted growth on (001) GaAs. <i>Physical Review Letters</i> , 1990, 64, 192-195.	2.9	108
140	Low retardance fused quartz window for real-time optical applications in ultrahigh vacuum. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1989, 7, 3291-3294.	0.9	73
141	Optical properties of copper-oxygen planes in superconducting oxides and related materials. <i>Physical Review B</i> , 1989, 40, 6797-6805.	1.1	98
142	Kinetic Limits of Monolayer Growth on (001) GaAs by Organometallic Chemical-vapor Deposition. <i>Physical Review Letters</i> , 1988, 61, 2782-2785.	2.9	137
143	Oxygen-deficiency-induced localized optical excitations in $\text{YBa}_2\text{Cu}_3\text{O}_x$ . <i>Physical Review B</i> , 1988, 38, 870-873.	1.1	100
144	Optical anisotropy of $\text{YBa}_2\text{Cu}_3\text{O}_{7-x}$ . <i>Physical Review B</i> , 1988, 38, 5077-5080.	1.1	72

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145	Application of reflectance difference spectroscopy to molecular-beam epitaxy growth of GaAs and AlAs. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1988, 6, 1327-1332.	0.9	499
146	Correlation of dopant-induced optical transitions with superconductivity in $\text{La}_{2-x}\text{Sr}_x\text{CuO}_4$ . <i>Physical Review B</i> , 1988, 37, 3396-3399.	1.1	73
147	Semiconductor topography in aqueous environments: Tunneling microscopy of chemomechanically polished (001)-GaAs. <i>Applied Physics Letters</i> , 1987, 50, 1742-1744.	1.5	61
148	Substantially Transparent Pt, Pd, Rh, And Re Films: Preparation and Properties. <i>Materials Research Society Symposia Proceedings</i> , 1987, 111, 379.	0.1	2
149	Optical Reflectance and Rheed Transients During Mbe Growth on (001) GaAs. <i>Materials Research Society Symposia Proceedings</i> , 1987, 91, 57.	0.1	6
150	Optical reflectance and electron diffraction studies of molecular-beam-epitaxy growth transients on GaAs(001). <i>Physical Review Letters</i> , 1987, 59, 1687-1690.	2.9	215
151	Multiple determination of the optical constants of thin-film coating materials: a Rh sequel. <i>Applied Optics</i> , 1986, 25, 1299.	2.1	17
152	Optical properties of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ . <i>Journal of Applied Physics</i> , 1986, 60, 754-767.	1.1	830
153	Microstructurally engineered, optically transmissive, electrically conductive metal films. <i>Journal of Applied Physics</i> , 1986, 60, 3028-3034.	1.1	33
154	Grain-size effects in the parallel-band absorption spectrum of aluminum. <i>Physical Review B</i> , 1986, 33, 5363-5367.	1.1	18
155	Experiment and theory of "transparent" metal films. <i>Nature</i> , 1985, 313, 664-666.	13.7	26
156	Anisotropies in the Above-Band-Gap Optical Spectra of Cubic Semiconductors. <i>Physical Review Letters</i> , 1985, 54, 1956-1959.	2.9	404
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